

DSK9J01×0L

Silicon N-channel Junction FET

For low frequency amplification / For piezoelectric sensor
DSK5J01 in SSMini3 type package

■ Features

- High gate-drain Voltage (Source open) V_{GD0}
- Halogen-free / RoHS compliant
(EU RoHS / UL-94 V-0 / MSL: Level 1 compliant)

■ Marking Symbol: B6

■ Packaging

Embossed type (Thermo-compression sealing) : 3 000 pcs / reel (standard)

■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Rating	Unit
Gate-drain voltage (Source short)	VGDS	-55	V
Drain current	ID	30	mA
Gate current	IG	10	mA
Power dissipation	PD	125	mW
Channel temperature	T _{ch}	150	°C
Operating ambient temperature	T _{opr}	-40 to +85	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25 °C ± 3 °C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Gate-drain voltage (Source short)	VGDS	IG = -100 μA, V _{DS} = 0	-55			V
Drain current *1	IDSS	V _{DS} = 10 V, V _{GS} = 0	1.0		6.5	mA
Gate-source cutoff current	IGSS	V _{GS} = -30 V, V _{DS} = 0			-10	nA
Gate-source cutoff voltage	VGSC	V _{DS} = 10 V, ID = 10 μA			-5	V
Forward transfer admittance	Y _{fs}	V _{DS} = 10 V, ID = 5 mA, f = 1 kHz	2.5	7.5		mS
Small-signal short-circuit input capacitance	C _{iss}	V _{DS} = 10 V, V _{GS} = 0, f = 1 MHz		6.0		pF
Small-signal reverse transfer capacitance	C _{rss}			2.5		pF

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

*1 Rank classification

Code	P	Q
Rank	P	Q
IDSS (mA)	1.0 to 3.0	2.0 to 6.5
Marking symbol	B6P	B6Q

